

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $R_{DS(on)}$ and to ensure minimal power loss and heat dissipation.

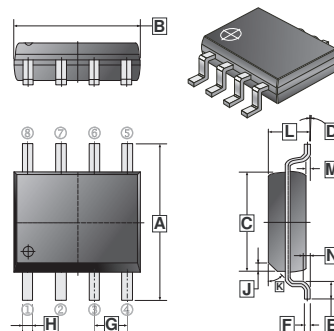
FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe SOP-8 saves board space
- Fast switching speed
- High performance trench technology

APPLICATION

DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones

SOP-8

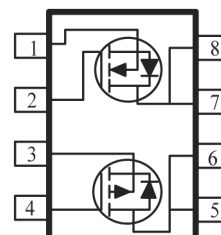


REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.8	6.20	H	0.35	0.51
B	4.80	5.00	J	0.375 REF.	
C	3.80	4.00	K	45°	
D	0°	8°	L	1.35	1.75
E	0.50	0.93	M	0.10	0.25
F	0.19	0.25	N	0.25 REF.	
G	1.27 TYP.				

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8	2.5K	13 inch

Top View



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Rating		Unit
			N-CH	P-CH	
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Continuous Drain Current ¹	T _A = 25°C	I _D	5.3	-5.2	A
	T _A = 70°C		4.2	-4.1	A
Pulsed Drain Current ²		I _{DM}	20	-20	A
Continuous Source Current (Diode Conduction) ¹		I _S	1.3	-1.3	A
Total Power Dissipation ¹	T _A = 25°C	P _D	2.1		W
	T _A = 70°C		1.3		W
Operating Junction & Storage Temperature Range		T _J , T _{STG}	-55 ~ 150		°C
Thermal Resistance Ratings					
Maximum Junction-to-Ambient ¹	t ≤ 10 sec	R _{θJA}	62.5		°C / W
	Steady State		110		°C / W

Notes:

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ch	Min.	Typ.	Max.	Unit	Teat Conditions
Static							
Gate Threshold Voltage	V _{GS(th)}	N	1.2	1.7	2.5	V	V _{DS} =V _{GS} , I _D =250μA
		P	-1.2	-1.8	-2.5		V _{DS} =V _{GS} , I _D = -250μA
Gate-Body Leakage	I _{GSS}	N	-	±80	±100	nA	V _{DS} =0, V _{GS} =20V
		P	-	±80	±100		V _{DS} =0, V _{GS} = -20V
Zero Gate Voltage Drain Current	I _{DSS}	N	-	0.8	1	μA	V _{DS} =24V, V _{GS} =0
		P	-	-0.8	-1		V _{DS} = -24V, V _{GS} =0
On-State Drain Current ¹	I _{D(on)}	N	20	24	-	A	V _{DS} =5V, V _{GS} =10V
		P	-20	-24	-		V _{DS} = -5V, V _{GS} = -10V
Drain-Source On-Resistance ¹	R _{DS(ON)}	N	-	43	50	mΩ	V _{GS} =10V, I _D =5.3A
			-	70	82		V _{GS} =4.5V, I _D =4.2A
		P	-	45	52		V _{GS} = -10V, I _D = -5.2A
			-	72	80		V _{GS} = -4.5V, I _D = -4.2A
Diode Forward Voltage	V _{SD}	N	-	0.75	-	V	V _{GS} =0, I _S =1.3A
		P	-	-0.88	-		V _{GS} =0, I _S = -1.3A
Dynamic ²							
Total Gate Charge	Q _g	N	-	2.2	-	nC	N-Channel I _D =5.3A, V _{DS} =15V, V _{GS} =10V P-Channel I _D = -5.2A, V _{DS} = -10V, V _{GS} = -15V
		P	-	10	-		
Gate-Source Charge	Q _{gs}	N	-	0.5	-		
		P	-	2.2	-		
Gate-Drain Charge	Q _{gd}	N	-	0.8	-		
		P	-	1.7	-		
Turn-On Delay Time	T _{d(on)}	N	-	8	-	nS	N-Channel V _{DD} =15V, V _{GEN} =10V I _D =1A, R _{GEN} =6Ω P-Channel V _{DD} = -15V, V _{GEN} = -10V I _D = -1A, R _{GEN} =6Ω
		P	-	10	-		
Rise Time	T _r	N	-	5	-		
		P	-	2.8	-		
Turn-Off Delay Time	T _{d(off)}	N	-	23	-		
		P	-	53.6	-		
Fall Time	T _f	N	-	3	-		
		P	-	46	-		

Notes:

1. Pulse test : $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

CHARACTERISTIC CURVES (N-Channel)

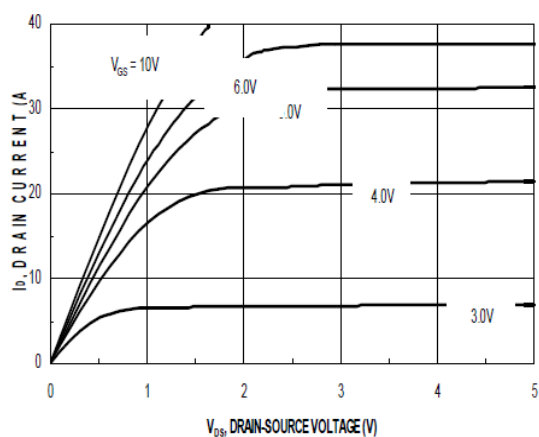


Figure 1. On-Region Characteristics

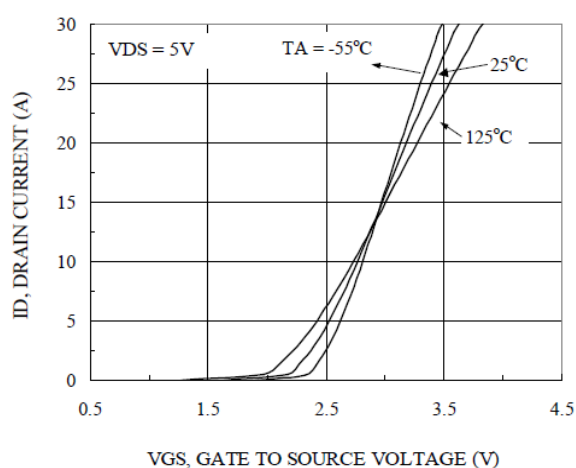


Figure 2. Body Diode Forward Voltage Variation with Source Current and Temperature

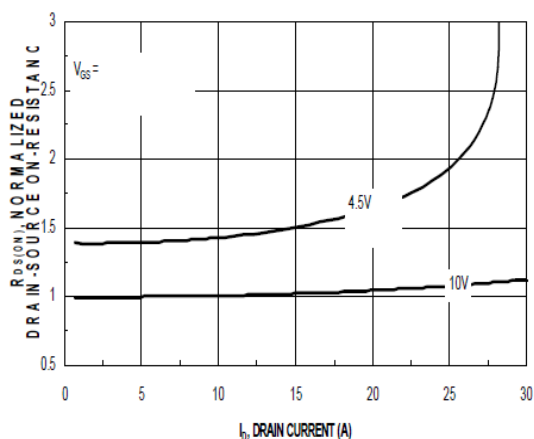


Figure 3. On Resistance Vs Vgs Voltage

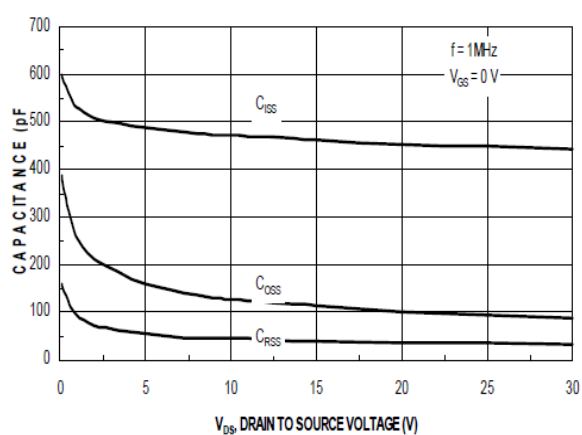


Figure 4. Capacitance Characteristics

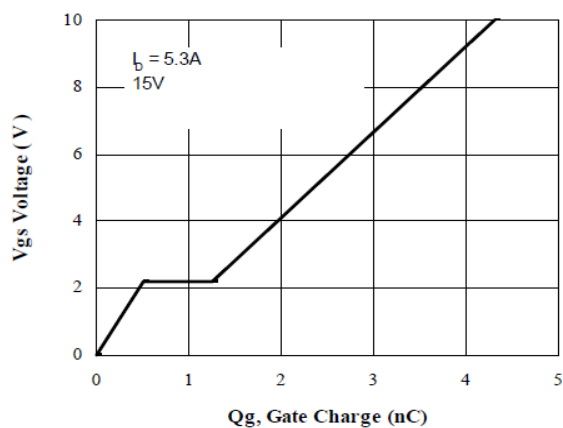


Figure 5. Gate Charge Characteristics

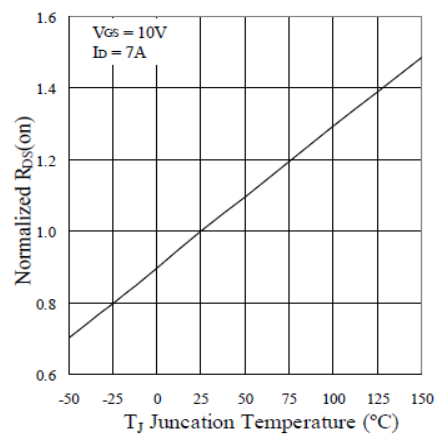


Figure 6. On-Resistance Variation with Temperature

CHARACTERISTIC CURVES

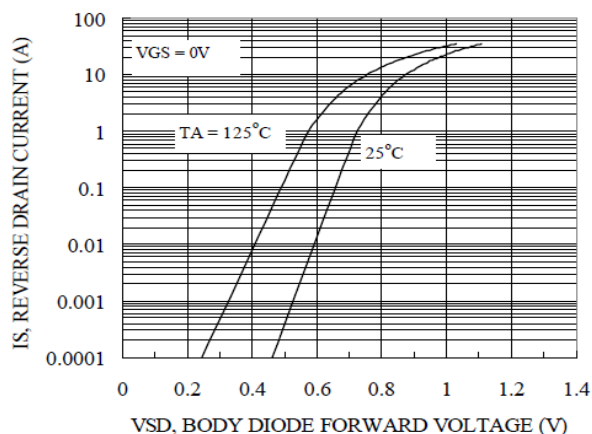


Figure 7. Transfer Characteristics

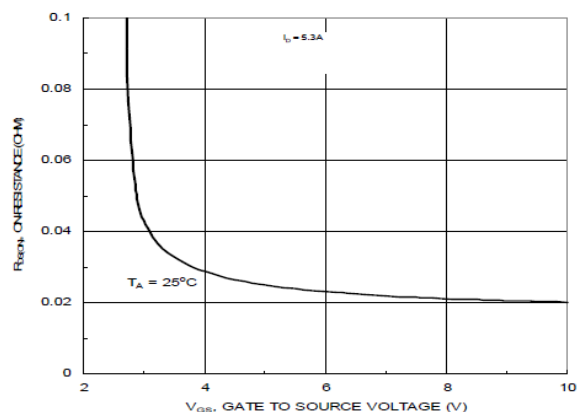


Figure 8. On-Resistance with Gate to Source Voltage

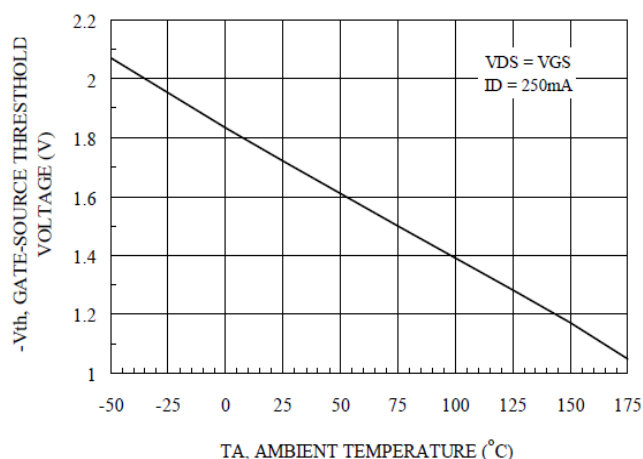


Figure 9. Vth Gate to Source Voltage Vs Temperature

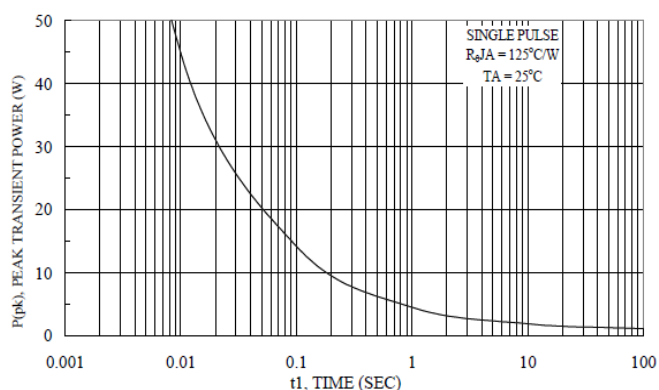


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

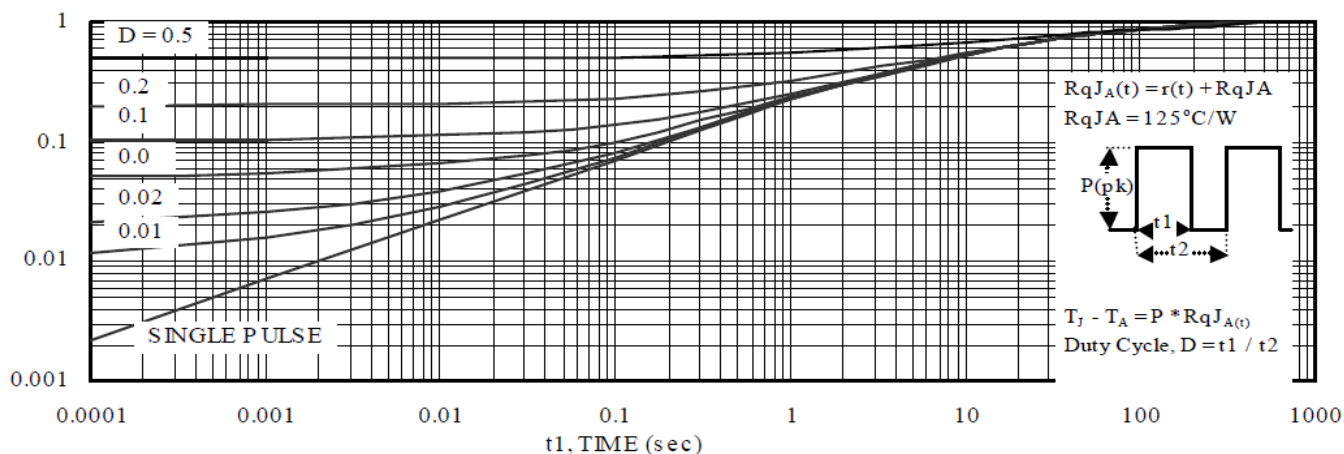


Figure 11. Transient Thermal Response Curve

CHARACTERISTIC CURVES (P-Channel)

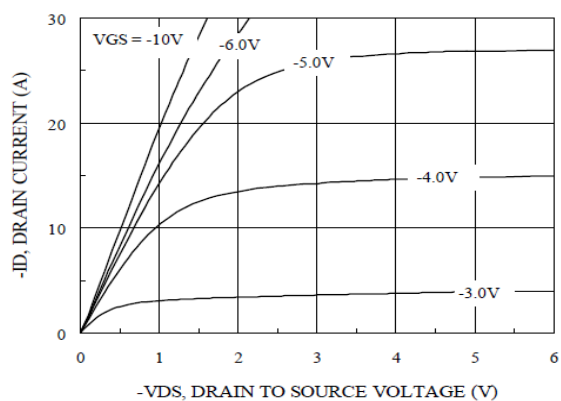


Figure 1. On-Region Characteristics

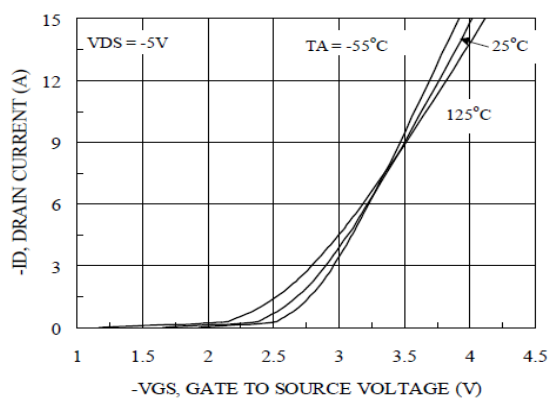


Figure 2. Body Diode Forward Voltage Variation with Source Current and Temperature

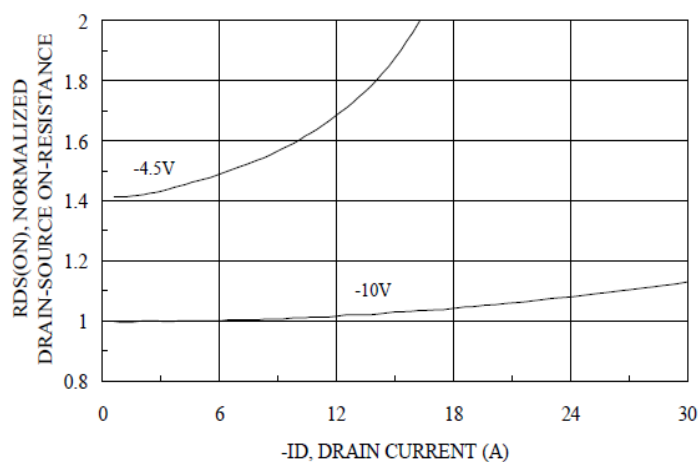


Figure 3. On Resistance Vs Vgs Voltage

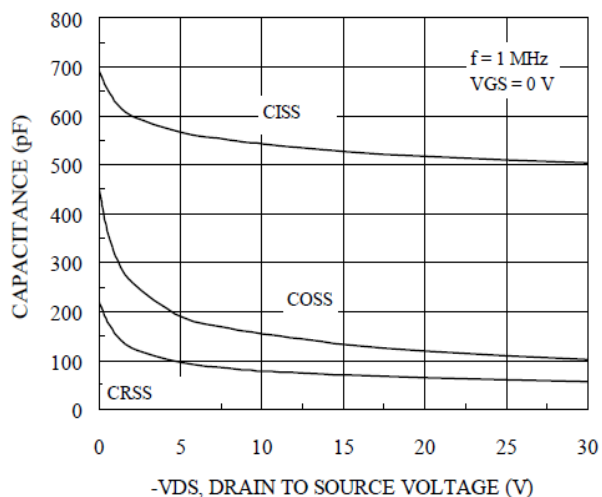


Figure 4. Capacitance Characteristics

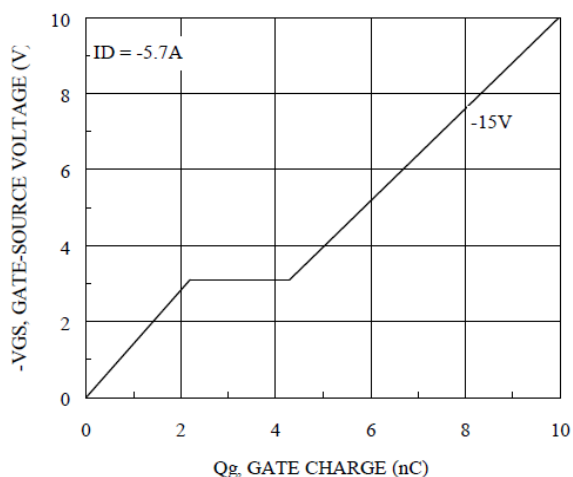


Figure 5. Gate Charge Characteristics

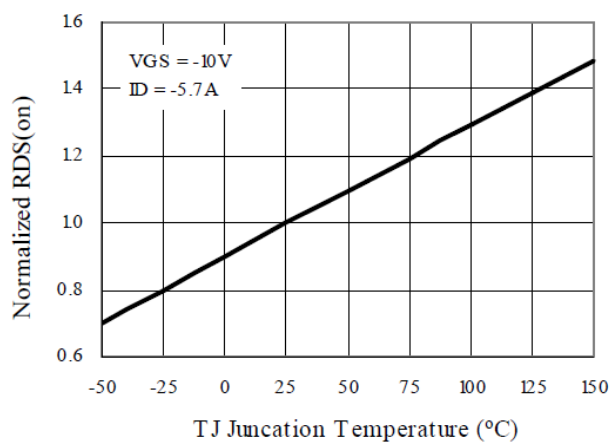


Figure 6. On-Resistance Variation with Temperature

CHARACTERISTIC CURVES

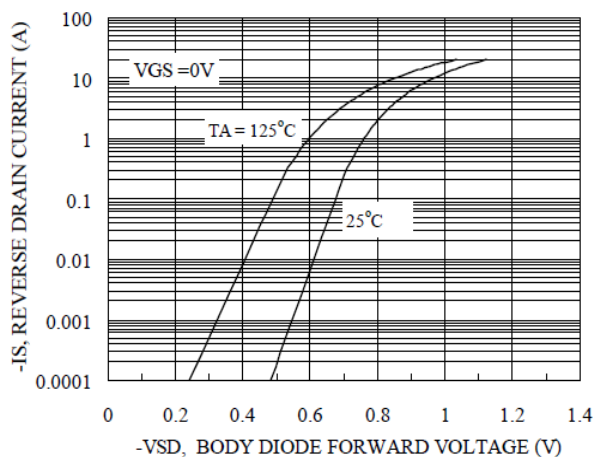


Figure 7. Transfer Characteristics

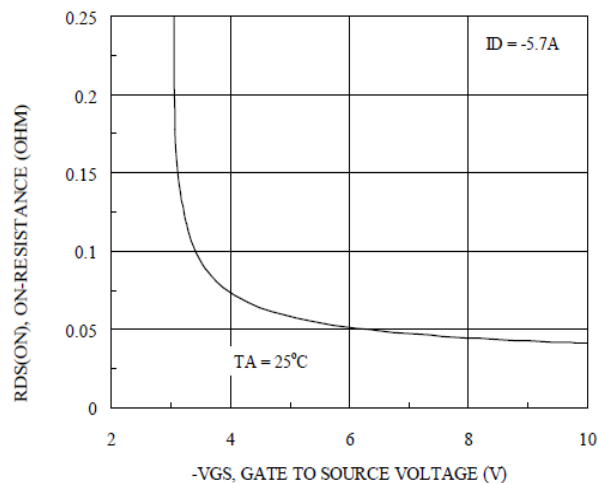


Figure 8. On-Resistance with Gate to Source Voltage

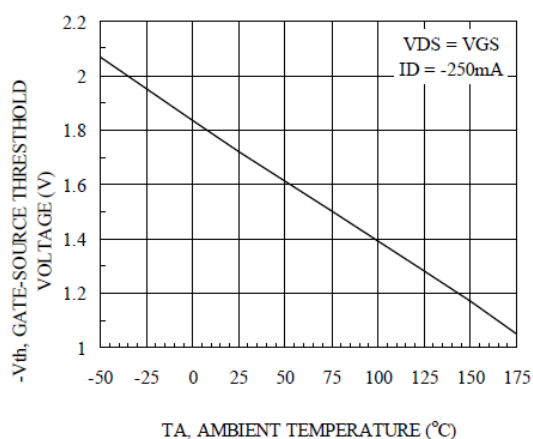


Figure 9. V_{th} Gate to Source Voltage Vs Temperature

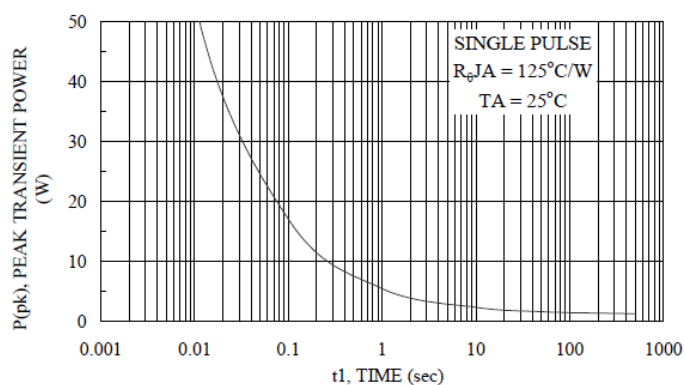


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

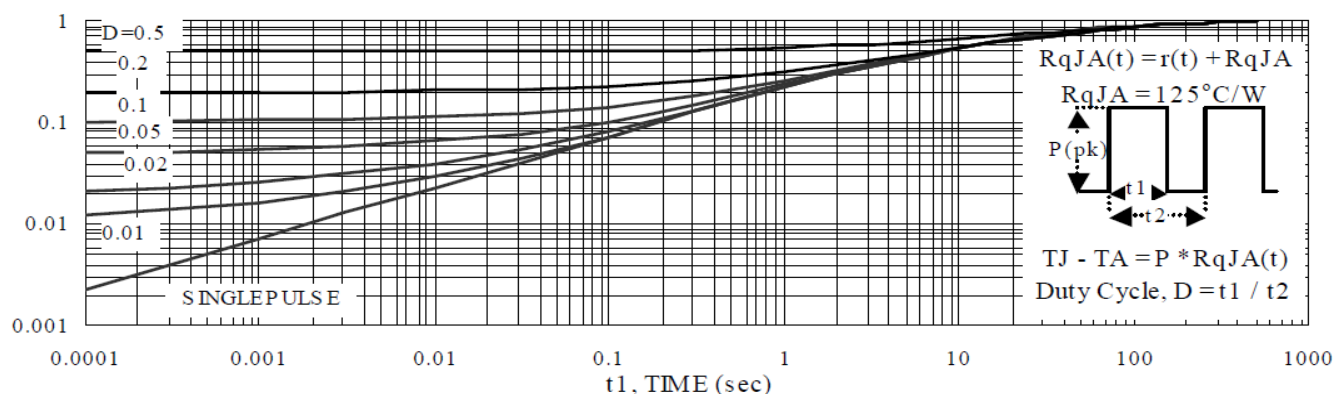


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